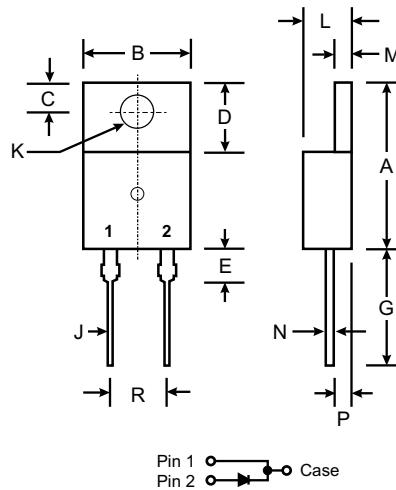


### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- Plastic Material: UL Flammability Classification Rating 94V-0

### Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Weight: 2.24 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



### Maximum Ratings and Electrical Characteristics

@  $T_A = 25^\circ\text{C}$  unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 830	MBR 835	MBR 840	MBR 845	MBR 850	MBR 860	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	30	35	40	45	50	60	V
RMS Reverse Voltage	$V_{R(\text{RMS})}$	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1) @ $T_C = 125^\circ\text{C}$	$I_O$			8.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$			150				A
Repetitive Peak Reverse Surge Current @ $t \leq 2.0\mu\text{s}$	$I_{RRM}$			1.0				A
Forward Voltage Drop @ $I_F = 8.0\text{A}$ , $T_C = 125^\circ\text{C}$ @ $I_F = 8.0\text{A}$ , $T_C = 25^\circ\text{C}$ @ $I_F = 16\text{A}$ , $T_C = 25^\circ\text{C}$	$V_{FM}$	0.57 0.70 0.84		0.70 0.80 0.95				V
Peak Reverse Current @ $T_C = 25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_C = 125^\circ\text{C}$	$I_{RM}$	0.1 15		0.1 15				mA
Typical Junction Capacitance (Note 2)	$C_j$			250				pF
Typical Thermal Resistance Junction to Case (Note 1)	$R_{\theta JC}$			3.0				K/W
Voltage Rate of Change (Rated $V_R$ )	$dV/dt$			1000				V/ $\mu\text{s}$
Operating and Storage Temperature Range	$T_j$ , $T_{STG}$			-65 to +150				°C

Notes: 1. Thermal resistance junction to case mounted on heatsink.  
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

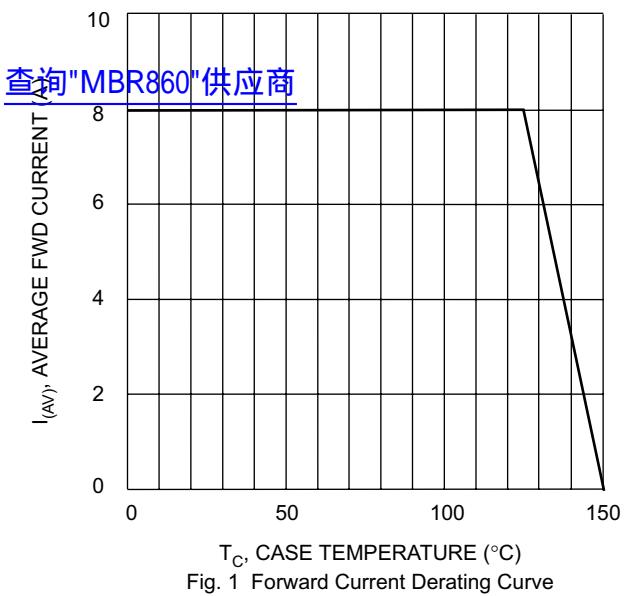


Fig. 1 Forward Current Derating Curve

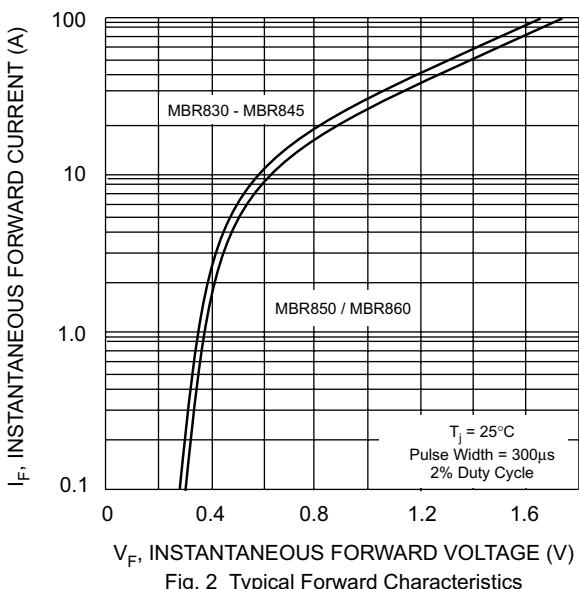


Fig. 2 Typical Forward Characteristics

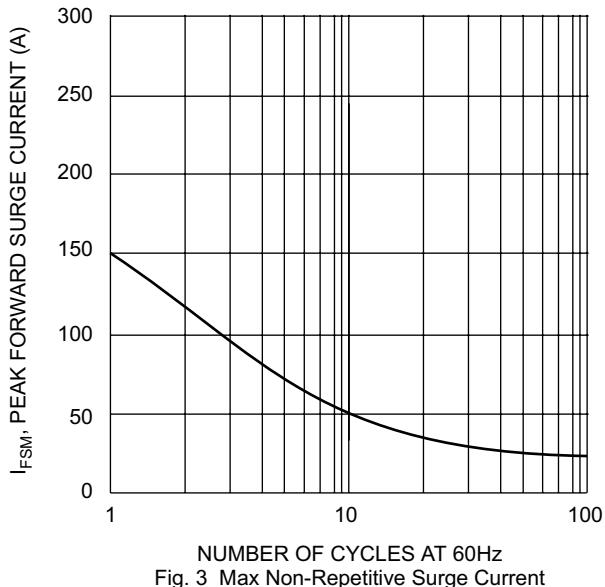


Fig. 3 Max Non-Repetitive Surge Current

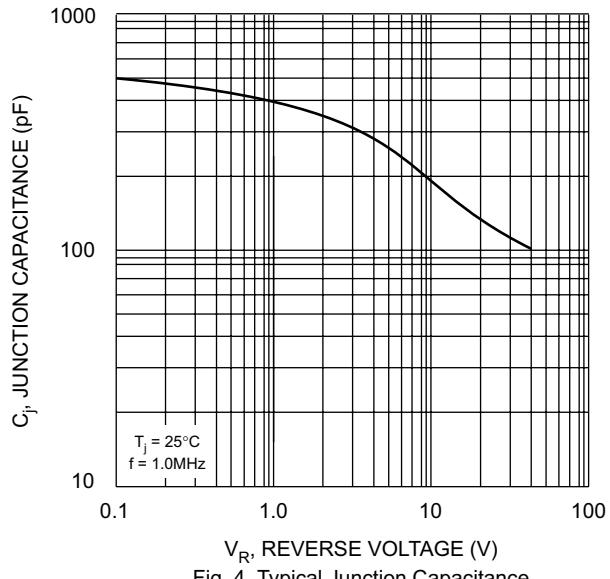


Fig. 4 Typical Junction Capacitance